AT24C256C

I²C-Compatible (2-Wire) Serial EEPROM
256-Kbit (32,768 x 8)

DATASHEET

Features

- Low-voltage and Standard-voltage Operation
  - V_{CC} = 1.7V to 5.5V
- Internally Organized as 32,768 x 8
- 2-wire Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bidirectional Data Transfer Protocol
- 400kHz (1.7V) and 1MHz (2.5V, 2.7V, 5.0V) Compatibility
- Write Protect Pin for Hardware Protection
- 64-byte Page Write Mode
  - Partial Page Writes Allowed
- Self-timed Write Cycle (5ms Max)
- High Reliability
  - Endurance: 1,000,000 Write Cycles
  - Data Retention: 40 Years
- Lead-free/Halogen-free Devices Available
- Green Package Options (Pb/Halide-free/RoHS Compliant)
  - 8-lead JEDEC SOIC, 8-lead TSSOP, 8-pad UDFN, and 8-ball VFBGA Packages
- Die Sale Options: Wafer Form, Waffle Pack, and Bumped Wafers

Description

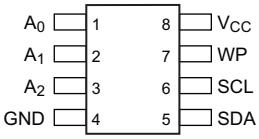
The Atmel® AT24C256C provides 262,144-bits of Serial Electrically Erasable and Programmable Read-Only Memory (EEPROM) organized as 32,768 words of 8 bits each. The device's cascading feature allows up to eight devices to share a common 2-wire bus. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The devices are available in space-saving 8-lead JEDEC SOIC, 8-lead TSSOP, 8-pad UDFN, and 8-ball VFBGA packages. In addition, this device operates from 1.7V to 5.5V.

1. Pin Configurations and Pinouts

Table 1-1. Pin Configuration

Pin	Function
A_0	Address Input
A_1	Address Input
A_2	Address Input
GND	Ground
SDA	Serial Data
SCL	Serial Clock Input
WP	Write Protect
V_{CC}	Device Power Supply

8-lead SOIC

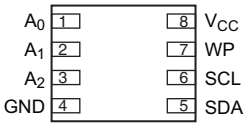


Top View

8-lead TSSOP

Top View

8-pad UDFN



Top View

8-ball VFBGA

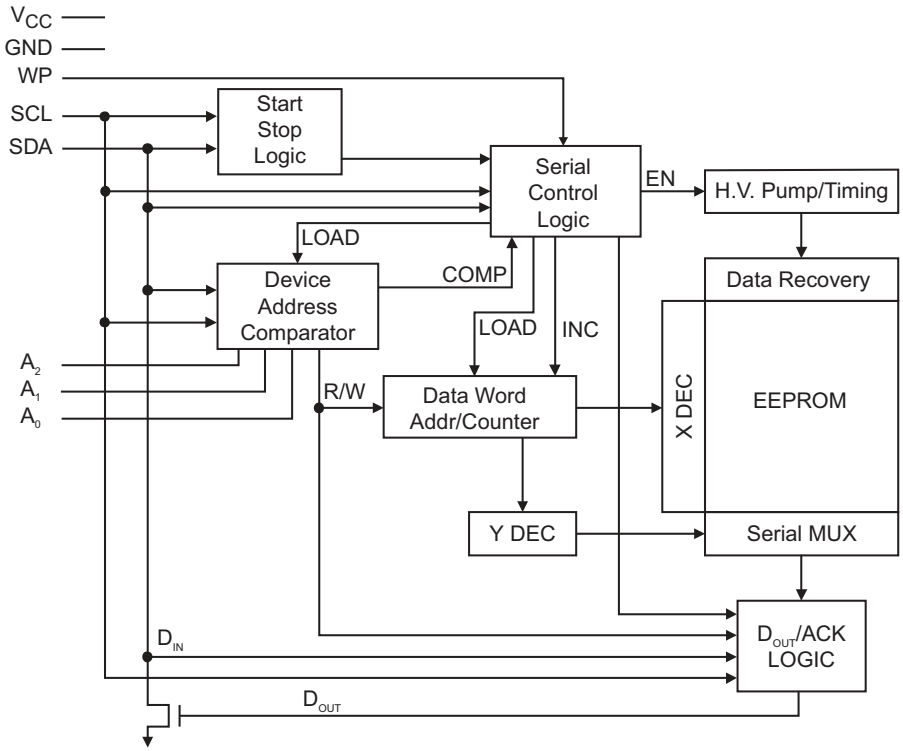
Bottom View

2. Absolute Maximum Ratings*

Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to + 150°C
Voltage on any pin with respect to ground	-1.0 V +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	5.0mA

*Notice: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

3. Block Diagram



4. Pin Descriptions

Serial Clock (SCL): The SCL input is used to positive-edge clock data into each EEPROM device and negative-edge clock data out of each device.

Serial Data (SDA): The SDA pin is bidirectional for serial data transfer. This pin is open drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

Device Addresses (A_2, A_1, A_0): The A_2, A_1, and A_0 pins are device address inputs that are hard wired (directly to GND or to V_{CC}) for compatibility with other Atmel AT24C devices. When the pins are hard wired, as many as eight 256K devices may be addressed on a single bus system. (Device addressing is discussed in detail in Section 7. “Device Addressing” on page 9). A device is selected when a corresponding hardware and software match is true. If these pins are left floating, the A_2, A_1, and A_0 pins will be internally pulled down to GND. However, due to capacitive coupling that may appear during customer applications, Atmel recommends always connecting the address pins to a known state. When using a pull-up resistor, Atmel recommends using 10kΩ or less.

Write Protect (WP): The Write Protect input, when connected to GND, allows normal write operations. When WP is connected directly to V_{CC}, all write operations to the memory are inhibited. If the pin is left floating, the WP pin will be internally pulled down to GND. However, due to capacitive coupling that may appear during customer applications, Atmel recommends always connecting the WP pins to a known state. When using a pull-up resistor, Atmel recommends using 10kΩ or less.

Table 4-1. Write Protect

WP Pin Status	Part of the Array Protected
At V_{CC}	Full Array
At GND	Normal Read/Write Operations

5. Memory Organization

AT24C256C, 256K Serial EEPROM: The 256K is internally organized as 512 pages of 64-bytes each. Random word addressing requires a 15-bit data word address.

5.1 Pin Capacitance

Table 5-1. Pin Capacitance[1]

Applicable over recommended operating range from: T_A = 25°C, f = 1.0MHz, V_{CC} = 1.7V to 5.5V.

Symbol	Test Condition	Max	Units	Conditions
$C_{I/O}$	Input/Output Capacitance (SDA)	8	pF	$V_{I/O}$ = 0V
C_{IN}	Input Capacitance (A_0, A_1, A_2, and SCL)	6	pF	V_{IN} = 0V

Note: 1. This parameter is characterized and is not 100% tested.

5.2 DC Characteristics

Table 5-2. DC Characteristics

Applicable over recommended operating range from: T_{AI} = - 40°C to +85°C, V_{CC} = 1.7V to 5.5V (unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Typ	Max	Units
V_{CC1}	Supply Voltage			1.7		5.5	V
I_{CC1}	Supply Current	V_{CC} = 5.0V	Read at 400kHz		1.0	2.0	mA
I_{CC2}	Supply Current	V_{CC} = 5.0V	Write at 400kHz		2.0	3.0	mA
I_{SB1}	Standby Current	V_{CC} = 1.7V	V_{IN} = V_{CC} or V_{SS}			1.0	µA
		V_{CC} = 5.0V				6.0	µA
I_{LI}	Input Leakage Current V_{CC} = 5.0V	V_{IN} = V_{CC} or V_{SS}			0.10	3.0	µA
I_{LO}	Output Leakage Current V_{CC} = 5.0V	V_{OUT} = V_{CC} or V_{SS}			0.05	3.0	µA
V_{IL}	Input Low Level[1]			-0.6		V_{CC} x 0.3	V
V_{IH}	Input High Level[1]			V_{CC} x 0.7		V_{CC} + 0.5	V
V_{OL1}	Output Low Level	V_{CC} = 1.7V	I_{OL} = 0.15mA			0.2	V
V_{OL2}	Output Low Level	V_{CC} = 3.0V	I_{OL} = 2.1mA			0.4	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

5.3 AC Characteristics

Table 5-3. AC Characteristics (Industrial Temperature)

Applicable over recommended operating range from: T_{AI} = -40°C to +85°C, V_{CC} = 1.7V to 5.5V, CL = 100 pF *(unless otherwise noted)*. Test conditions are listed in Note 2.

Symbol	Parameter	1.7V		2.5V, 5.0V		Units
		Min	Max	Min	Max	
f_{SCL}	Clock Frequency, SCL		400		1000	kHz
t_{LOW}	Clock Pulse Width Low	1300		400		ns
t_{HIGH}	Clock Pulse Width High	600		400		ns
t_I	Noise Suppression Time(1)		100		50	ns
t_{AA}	Clock Low to Data Out Valid	50	900	50	550	ns
t_{BUF}	Time the bus must be free before a new transmission can start(1)	1300		500		ns
$t_{HD.STA}$	Start Hold Time	600		250		ns
$t_{SU.STA}$	Start Set-up Time	600		250		ns
$t_{HD.DAT}$	Data In Hold Time	0		0		ns
$t_{SU.DAT}$	Data In Set-up Time	100		100		ns
t_R	Inputs Rise Time(1)		300		300	ns
t_F	Inputs Fall Time(1)		300		100	ns
$t_{SU.STO}$	Stop Set-up Time	600		250		ns
t_{DH}	Data Out Hold Time	50		50		ns
t_{WR}	Write Cycle Time		5		5	ms
Endurance(1)	25°C, Page Mode, 3.3V	1,000,000				Write Cycles

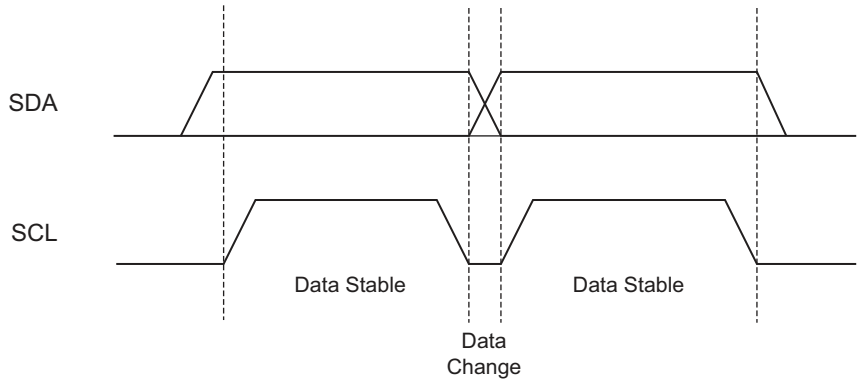
Notes: 1. This parameter is ensured by characterization and is not 100% tested.

2. AC measurement conditions:
   - R_L (connects to V_{CC}): 1.3kΩ (2.5V, 5.5V), 10kΩ (1.7V)
   - Input pulse voltages: $0.3V_{CC}$ to $0.7V_{CC}$
   - Input rise and fall times: ≤ 50ns
   - Input and output timing reference voltages: 0.5 x V_{CC}

6. Device Operation

Clock and Data Transitions: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods. Data changes during SCL high periods will indicate a start or stop condition as defined below.

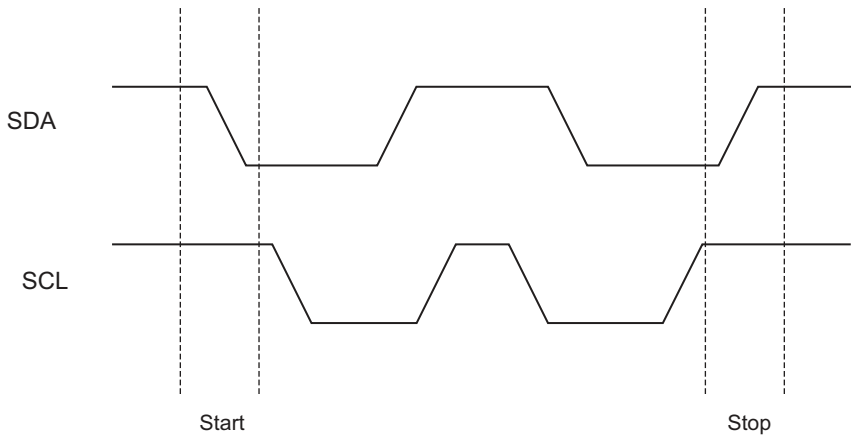
Figure 6-1. Data Validity



Start Condition: A high-to-low transition of SDA with SCL high is a start condition that must precede any other command.

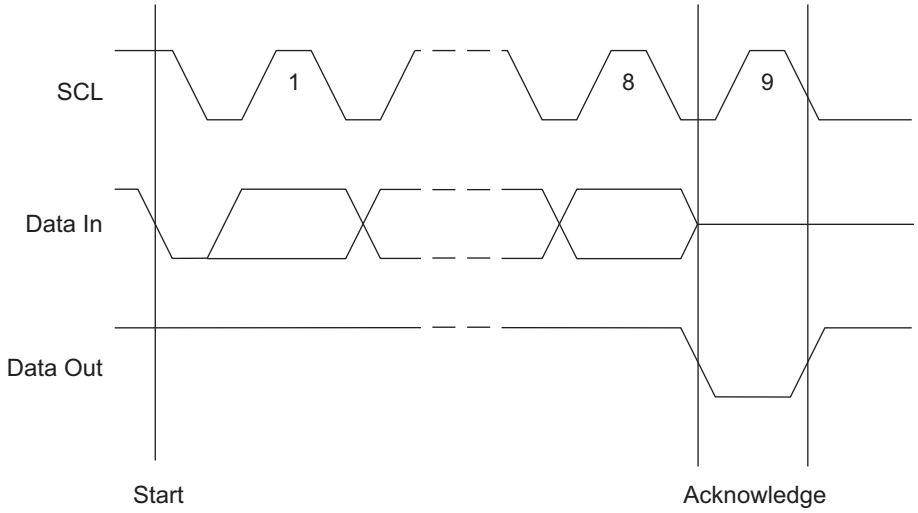
Stop Condition: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode.

Figure 6-2. Start and Stop Definition



Acknowledge: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a zero during the ninth clock cycle to acknowledge that it has received each word.

Figure 6-3. Output Acknowledge



Standby Mode: AT24C256C features a low-power standby mode that is enabled upon power-up and after the receipt of the Stop condition and the completion of any internal operations.

Software Reset: After an interruption in protocol, power-loss or system reset, any 2-wire part can be protocol reset by following these steps:

1. Create a Start condition (if possible).
2. Clock nine cycles.
3. Create another Start condition followed by Stop condition as shown below.

The device should be ready for the next communication after above steps have been completed. In the event that the device is still non-responsive or remains active on the SDA bus, a power cycle must be used to reset the device.

Figure 6-4. Software Reset

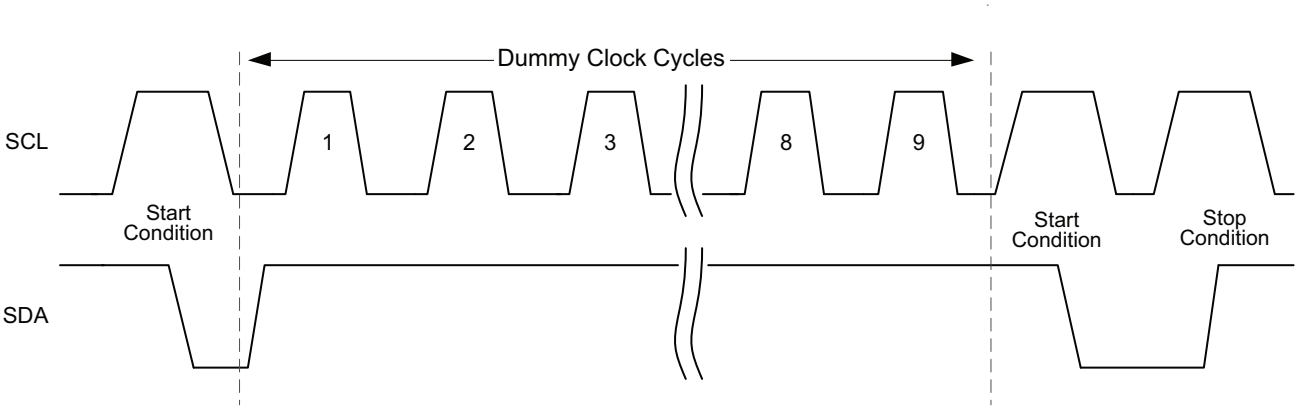


Figure 6-5. Bus Timing

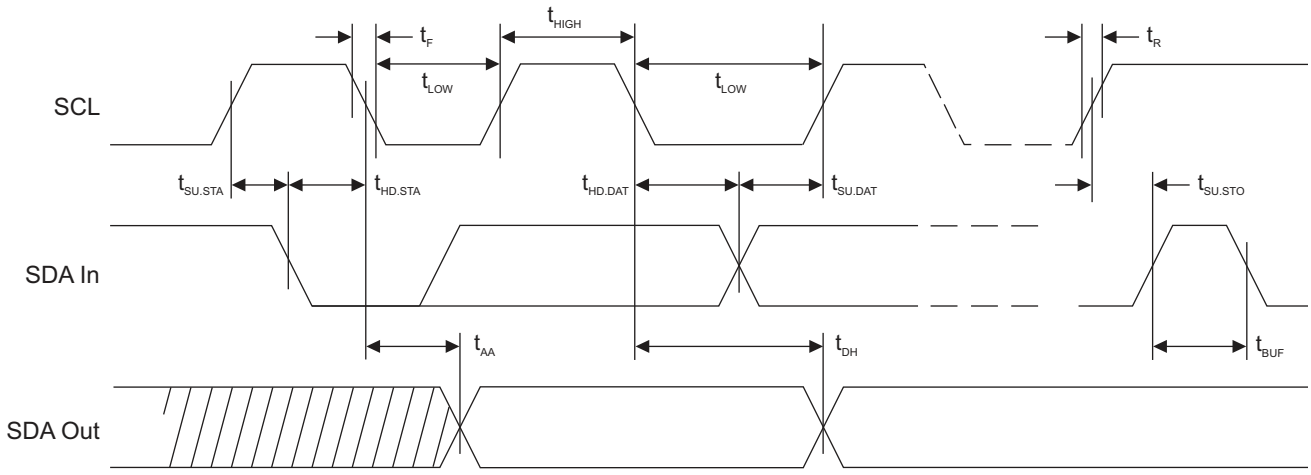
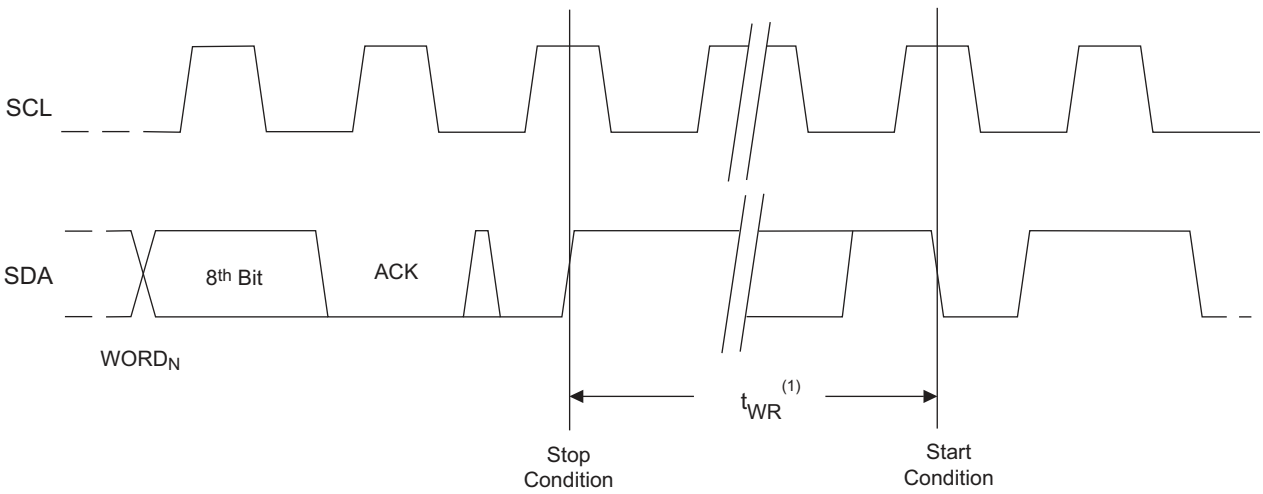


Figure 6-6. Write Cycle Timing

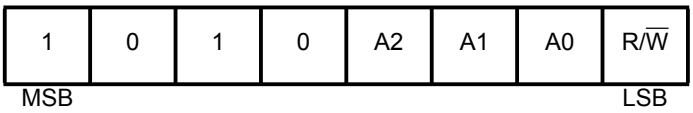


Note: 1. The write cycle time t_{WR} is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

7. Device Addressing

The 256K EEPROM requires an 8-bit device address word following a start condition to enable the chip for a read or write operation. The device address word consists of a mandatory one, zero sequence for the first four most significant bits as shown. This is common to all 2-wire EEPROM devices.

Figure 7-1. Device Addressing



The next three bits are the A2, A1, and A0 device address bits to allow as many as eight devices on the same bus. These bits must compare to their corresponding hard wired input pins. The A_2, A_1, and A_0 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high, and a write operation is initiated if this bit is low.

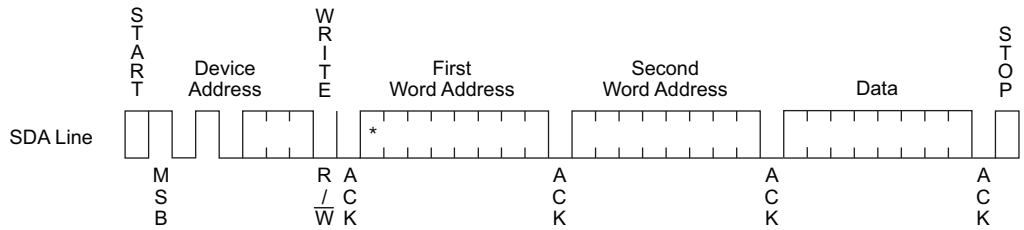
Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the device will return to a standby state.

Data Security: The AT24C256C has a hardware data protection scheme that allows the user to write protect the whole memory when the WP pin is at V_{CC}.

8. Write Operations

Byte Write: A Write operation requires two 8-bit data word addresses following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero, and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero. The addressing device, such as a microcontroller, must then terminate the write sequence with a Stop condition. At this time, the EEPROM enters an internally-timed write cycle, t_{WR}, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete.

Figure 8-1. Byte Write

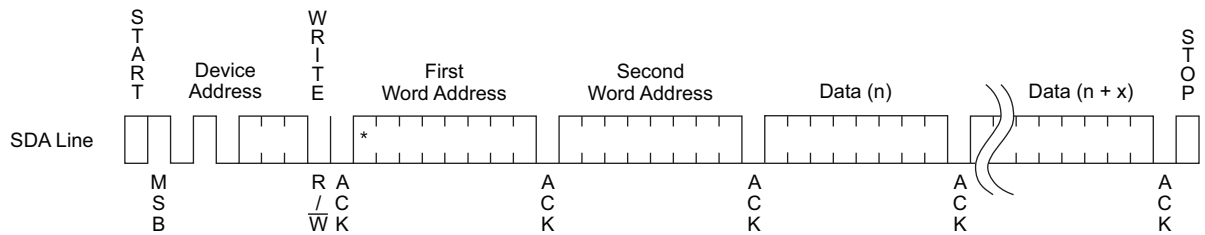


Note: * = Don't care bit

Page Write: The 256K EEPROM is capable of 64-byte page writes.

A Page Write is initiated the same way as a Byte Write, but the microcontroller does not send a Stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 63 more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a Stop condition .

Figure 8-2. Page Write



Note: * = Don't care bit

The data word address lower six bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 64 data words are transmitted to the EEPROM, the data word address will roll-over and the previous data will be overwritten. The address roll-over during write is from the last byte of the current page to the first byte of the same page.

Acknowledge Polling: Once the internally-timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a Start condition followed by the device address word. The Read/Write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero, allowing the read or write sequence to continue.

9. Read Operations

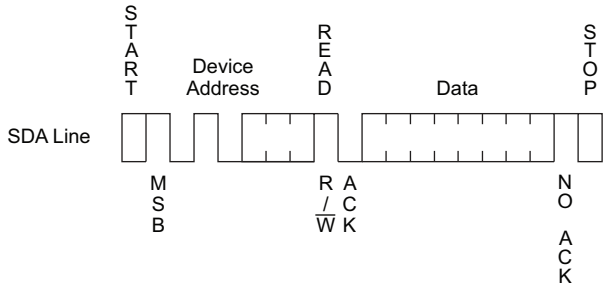
Read operations are initiated the same way as write operations with the exception that the Read/Write select bit in the device address word is set to one. There are three read operations:

- Current Address Read
- Random Address Read
- Sequential Read

Current Address Read: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address roll-over during read is from the last byte of the last memory page, to the first byte of the first page.

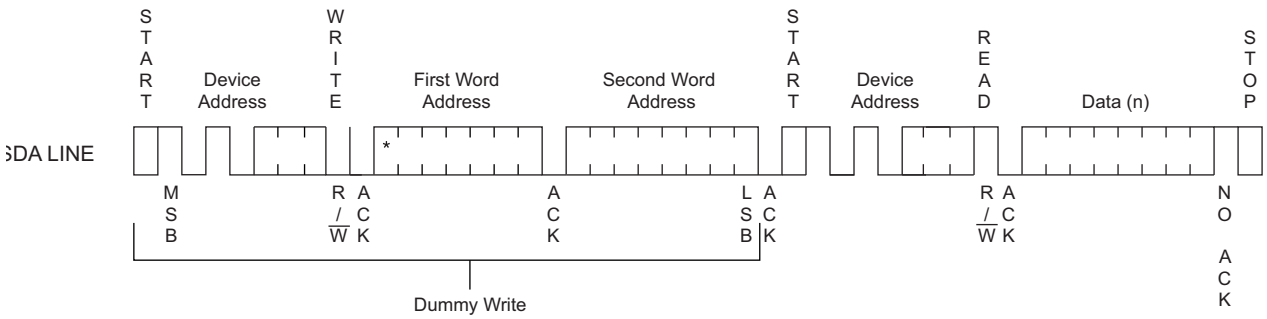
Once the device address with the Read/Write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition.

Figure 9-1. Current Address Read



Random Read: A Random Read requires a dummy byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a Current Address Read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following Stop condition.

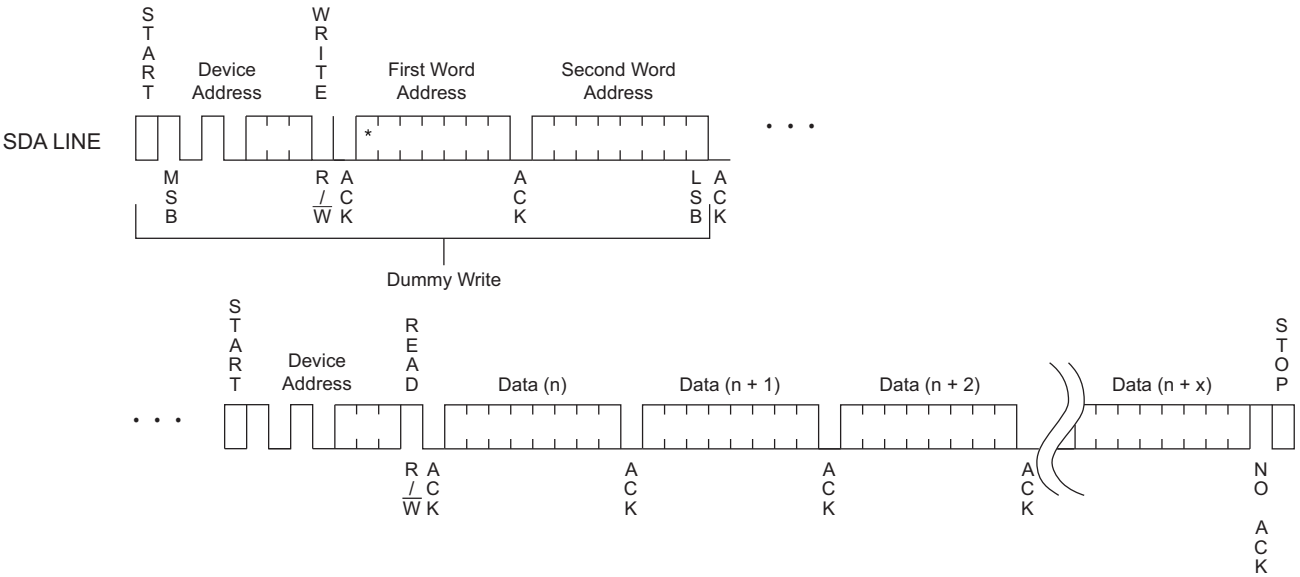
Figure 9-2. Random Read



Note: * = Don't care bit

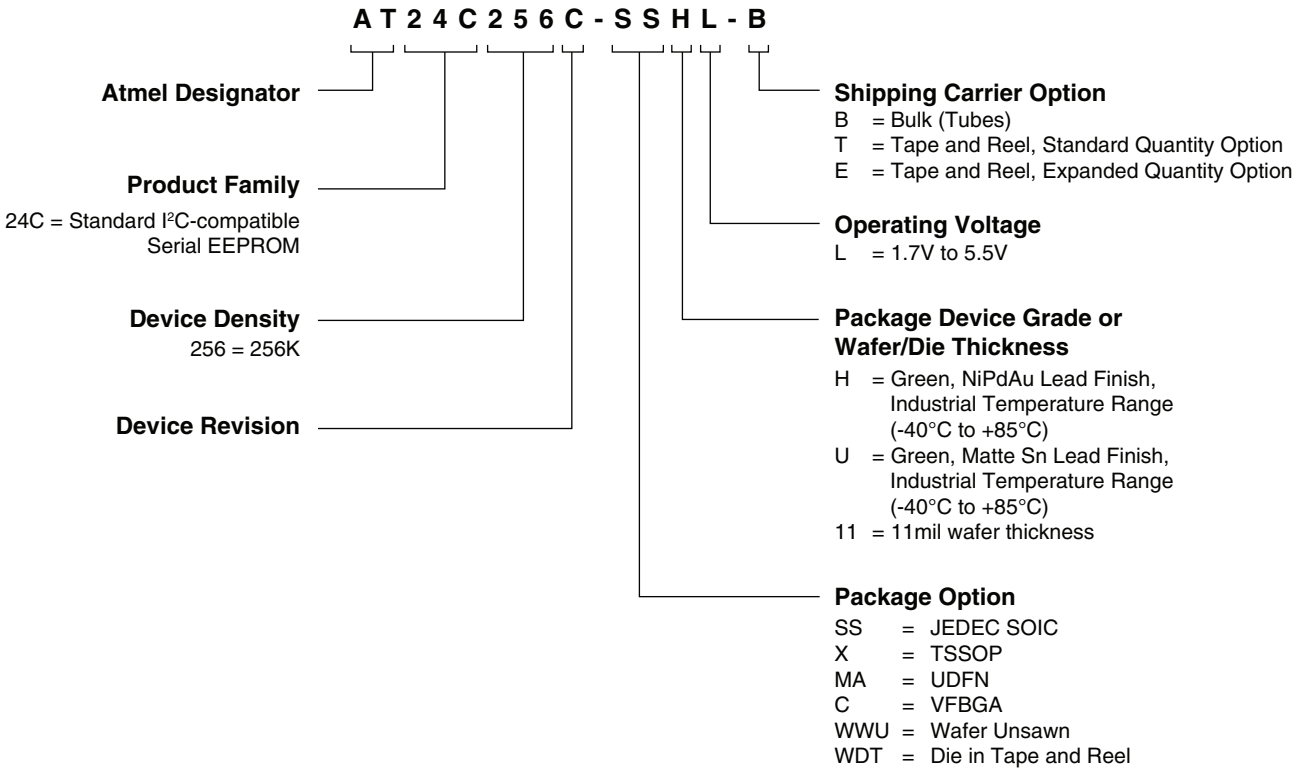
Sequential Read: Sequential Reads are initiated by either a Current Address Read or a Random Address Read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will roll-over, and the Sequential Read will continue. The Sequential Read operation is terminated when the microcontroller does not respond with a zero but does generate a following Stop condition.

Figure 9-3. Sequential Read



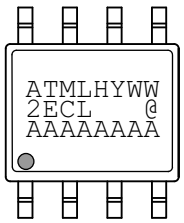
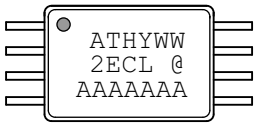
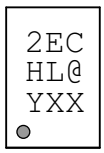
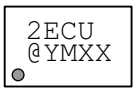
Note: * = Don’t care bit

10. Ordering Code Detail



11. Part Markings

AT24C256C: Package Marking Information

8-lead SOIC	8-lead TSSOP
	
8-lead UDFN	**8-ball VFBGA**
2.0 x 3.0 mm Body 	2.35 x 3.73 mm Body 

Note 1: ● designates pin 1

Note 2: Package drawings are not to scale

Catalog Number Truncation			
AT24C256C		Truncation Code ###: 2EC	
Date Codes			**Voltages**
Y = Year	M = Month	WW = Work Week of Assembly	L: 1.7V min
2: 2012 6: 2016 3: 2013 7: 2017 4: 2014 8: 2018 5: 2015 9: 2019	A: January B: February ... L: December	02: Week 2 04: Week 4 ... 52: Week 52	
Country of Assembly	**Lot Number**		**Grade/Lead Finish Material**
@ = Country of Assembly	AAA...A = Atmel Wafer Lot Number		U: Industrial/Matte Tin H: Industrial/NiPdAu
Trace Code			**Atmel Truncation**
XX = Trace Code (Atmel Lot Numbers Correspond to Code) Example: AA, AB.... YZ, ZZ			AT: Atmel ATM: Atmel ATML: Atmel

6/5/12

Atmel Package Mark Contact: DL-CSO-Assy_eng@atmel.com	TITLE	DRAWING NO.	REV.
	24C256CSM, AT24C256C Package Marking Information	24C256CSM	C

12. Ordering Information

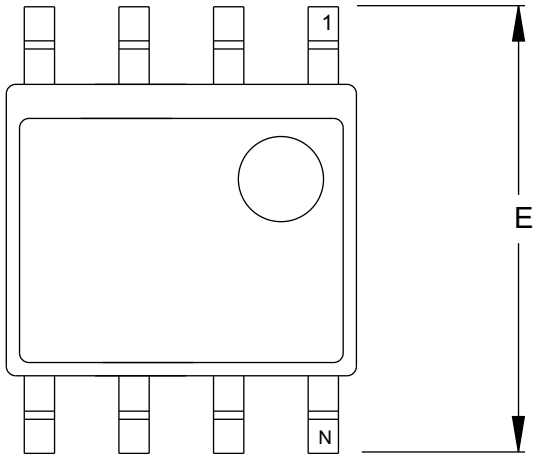
Atmel Ordering Code	Lead Finish	Package	Delivery Information		Operating Range
			Form	Quantity	
AT24C256C-SSHL-B	NiPdAu (Lead-free/Halogen-free)	8S1	Bulk (Tubes)	100 per Tube	Industrial Temperature (-40°C to 85°C)
AT24C256C-SSHL-T			Tape and Reel	4,000 per Reel	
AT24C256C-XHL-B		8X	Bulk (Tubes)	100 per Tube	
AT24C256C-XHL-T			Tape and Reel	5,000 per Reel	
AT24C256C-MAHL-T		8MA2	Tape and Reel	5,000 per Reel	
AT24C256C-MAHL-E			Tape and Reel	15,000 per Reel	
AT24C256C-CUL-T		8U2-1	Tape and Reel	5,000 per Reel	
AT24C256C-WWU11L[1]	N/A	Wafer Sale	Note 1		

Note: 1. Contact Atmel Sales for Wafer sales.

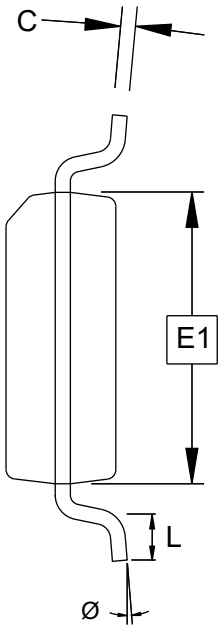
Package Type	
8S1	8-lead, 0.150” wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
8X	8-lead, 4.40mm body, Plastic Thin Shrink Small Outline Package (TSSOP)
8MA2	8-pad, 2.00mm x 3.00mm body, 0.50mm pitch, Dual No Lead (UDFN)
8U2-1	8-ball, Die Ball Grid Array Package (VFBGA)

13. Packaging Information

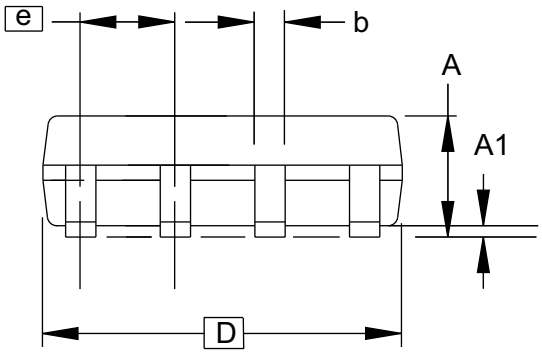
13.1 8S1 — 8-lead JEDEC SOIC



TOP VIEW



END VIEW



SIDE VIEW

Notes: This drawing is for general information only.
Refer to JEDEC Drawing MS-012, Variation AA
for proper dimensions, tolerances, datums, etc.

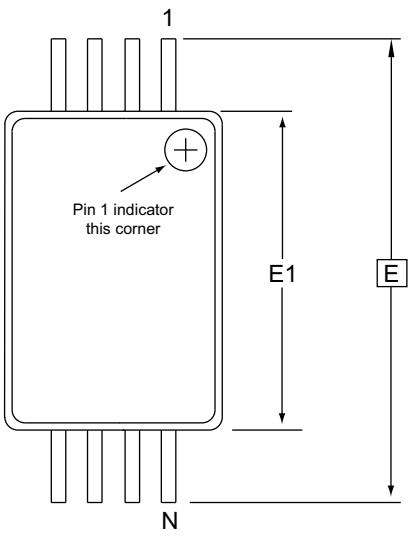
COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	1.35	–	1.75	
A1	0.10	–	0.25	
b	0.31	–	0.51	
C	0.17	–	0.25	
D	4.80	–	5.05	
E1	3.81	–	3.99	
E	5.79	–	6.20	
e	1.27 BSC			
L	0.40	–	1.27	
Ø	0°	–	8°	

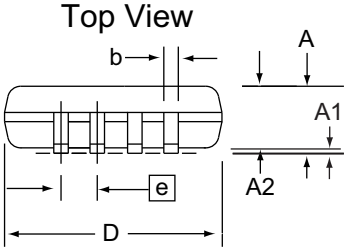
6/22/11

Atmel Package Drawing Contact: packagedrawings@atmel.com	TITLE 8S1, 8-lead (0.150” Wide Body), Plastic Gull Wing Small Outline (JEDEC SOIC)	GPC SWB	DRAWING NO. 8S1	REV. G

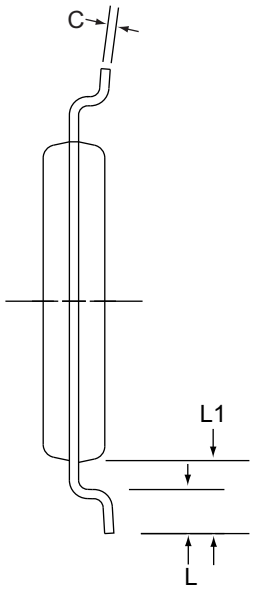
13.2 8X — 8-lead TSSOP



Top View



Side View



End View

Notes:
1. This drawing is for general information only. Refer to JEDEC Drawing MO-153, Variation AA, for proper dimensions, tolerances, datums, etc.
2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15mm (0.006in) per side.
3. Dimension E1 does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25mm (0.010in) per side.
4. Dimension b does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08mm total in excess of the b dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07mm.
5. Dimension D and E1 to be determined at Datum Plane H.

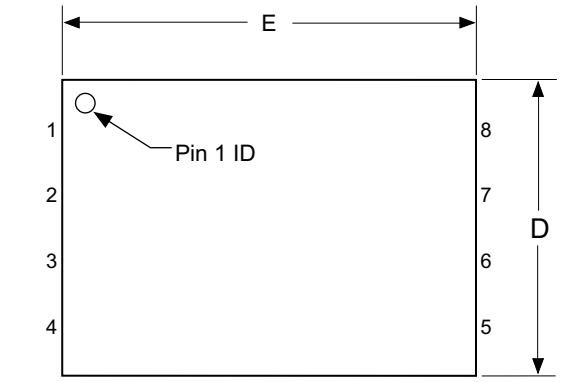
COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	-	-	1.20	
A1	0.05	-	0.15	
A2	0.80	1.00	1.05	
D	2.90	3.00	3.10	2, 5
E		6.40 BSC		
E1	4.30	4.40	4.50	3, 5
b	0.19	0.25	0.30	4
e		0.65 BSC		
L	0.45	0.60	0.75	
L1		1.00 REF		
C	0.09	-	0.20	

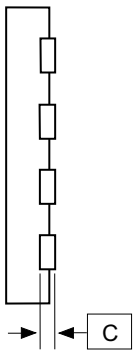
2/27/14

Atmel Package Drawing Contact: packagedrawings@atmel.com	**TITLE** 8X, 8-lead 4.4mm Body, Plastic Thin Shrink Small Outline Package (TSSOP)	**GPC** TNR	**DRAWING NO.** 8X	**REV.** E

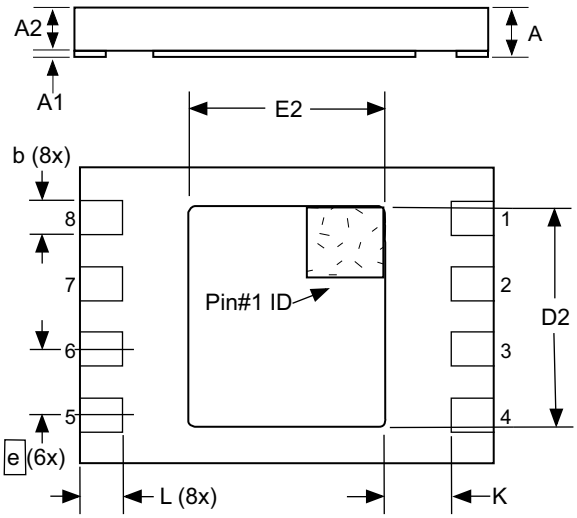
13.3 8MA2 — 8-pad UDFN



TOP VIEW



SIDE VIEW



BOTTOM VIEW

Notes:
1. This drawing is for general information only. Refer to Drawing MO-229, for proper dimensions, tolerances, datums, etc.
2. The Pin #1 ID is a laser-marked feature on Top View.
3. Dimensions b applies to metallized terminal and is measured between 0.15 mm and 0.30 mm from the terminal tip. If the terminal has the optional radius on the other end of the terminal, the dimension should not be measured in that radius area.
4. The Pin #1 ID on the Bottom View is an orientation feature on the thermal pad.

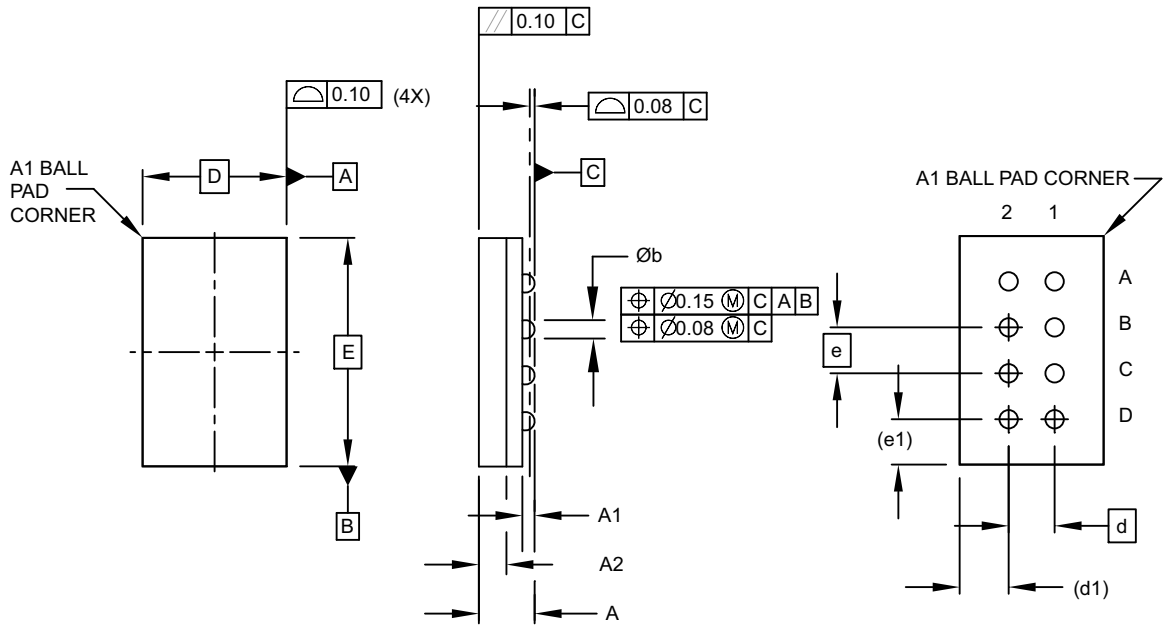
COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.50	0.55	0.60	
A1	0.0	0.02	0.05	
A2	-	-	0.55	
D	1.90	2.00	2.10	
D2	1.40	1.50	1.60	
E	2.90	3.00	3.10	
E2	1.20	1.30	1.40	
b	0.18	0.25	0.30	3
C	1.52 REF			
L	0.30	0.35	0.40	
e	0.50 BSC			
K	0.20	-	-	

11/26/14

Atmel Package Drawing Contact: packagedrawings@atmel.com	**TITLE** 8MA2, 8-pad 2 x 3 x 0.6mm Body, Thermally Enhanced Plastic Ultra Thin Dual Flat No-Lead Package (UDFN)	**GPC** YNZ	**DRAWING NO.** 8MA2	**REV.** G

13.4 8U2-1 — 8-ball VFBGA



TOP VIEW SIDE VIEW BOTTOM VIEW

8 SOLDER BALLS

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.81	0.91	1.00	
A1	0.15	0.20	0.25	
A2	0.40	0.45	0.50	
b	0.25	0.30	0.35	
D	2.35 BSC			
E	3.73 BSC			
e	0.75 BSC			
e1	0.74 REF			
d	0.75 BSC			
d1	0.80 REF			

Notes:

1. This drawing is for general
2. Dimension 'b' is measured at the maximum solder ball diameter.
3. Solder ball composition shall be 95.5Sn-4.0Ag-.5Cu.

6/11/13

Atmel Package Drawing Contact: packagedrawings@atmel.com	TITLE 8U2-1, 8-ball, 2.35 x 3.73 mm Body, 0.75 mm pitch, Very Thin, Fine-Pitch Ball Grid Array Package (VFBGA)	GPC GWW	DRAWING NO. 8U2-1	REV. G

14. Revision History

Doc. Rev.	Date	Comments
8568F	01/2015	Add the UDFN Expanded Quantity Option. Update 8X, 8MA2, and 8U2-1 package outline drawings, the ordering information section, and the disclaimer page.
8568E	08/2012	Update template and Atmel logo. Correct 8-lead UDFN to 8-pad UDFN. Update AC characteristics from µs to ns units and their respective values. Update part marking description.
8568D	09/2011	Atmel global device marking alignment. Update 8S1, 8A2 to 8X, 8MA2, and 8U2-1 package drawings.
8568C	05/2010	Update 8S1 and 8A2 package drawings.
8568B	03/2010	Part Markings and ordering detail/codes updated.
8568A	09/2009	Initial document release.

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